

METHOD OF FORMING VARIABLE OXIDE THICKNESSES
ACROSS SEMICONDUCTOR CHIPS

ABSTRACT OF THE INVENTION

5 A method for forming variable oxide thicknesses across semiconductor chips comprises providing a silicon semiconductor substrate having pre-selected areas open to silicon surface using a photoresist layer; immersing the silicon semiconductor substrate in an HF type electrolytic bath to produce a porous silicon area; and removing the photoresist layer and oxidizing the silicon semiconductor substrate to produce a plurality of thicknesses of gate oxide on the silicon semiconductor substrate.

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